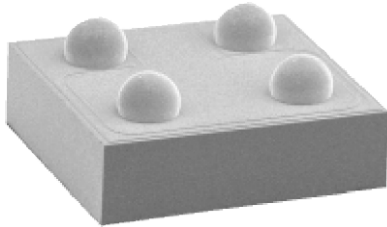


FlipKY[®], 1 A Chip Scale Package Schottky Barrier Rectifier


 FlipKY[®]
FEATURES

- Ultra low V_F per footprint area
- Low leakage
- Low thermal resistance
- One-fifth footprint of SMA
- Super low profile (0.6 mm)
- Available tested on tape and reel


**RoHS
COMPLIANT**
APPLICATIONS

- Reverse polarity protection
- Current steering
- Freewheeling
- Flyback
- Oring

DESCRIPTION

Vishay's FlipKY[®] product family utilizes wafer level chip scale packaging to deliver Schottky diodes with the lowest V_F to PCB footprint area in industry. The four bump 1.5 x 1.5 mm devices can deliver up to 1 A and occupy only 2.3 mm² of board space. The anode and cathode connections are made through solder bump pads on one side of the silicon enabling designers to strategically place the diodes on the PCB. This design not only minimizes board space but also reduces thermal resistance and inductance, which can improve overall circuit efficiency.

Typical applications include hand-held, portable equipment such as cell phones, MP3 players, bluetooth, GPS, PDAs, and portable hard disk drives where space savings and performance are crucial.

PRODUCT SUMMARY

$I_{F(AV)}$	1 A
V_R	30 V

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	MAX.	UNITS
V_{RRM}		30	V
$I_{F(AV)}$	Rectangular waveform	1	A
I_{FSM}		250	
V_F	1 Apk, $T_J = 125\text{ }^\circ\text{C}$	0.33	V
T_J		- 55 to 150	$^\circ\text{C}$

VOLTAGE RATINGS

PARAMETER	SYMBOL	FCSP130LTR	UNITS
Maximum DC reverse voltage	V_R	30	V
Maximum working peak reverse voltage	V_{RWM}		

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current	$I_{F(AV)}$	50 % duty cycle at $T_{PCB} = 120\text{ }^{\circ}\text{C}$, rectangular waveform		1.0	A
Maximum peak one cycle non-repetitive surge current at 25 °C	I_{FSM}	5 μs sine or 3 μs rect. pulse	Following any rated load condition and with rated V_{RRM} applied	220	
		10 ms sine or 6 ms rect. pulse		21	
Non-repetitive avalanche energy	E_{AS}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_{AS} = 2.0\text{ A}$, $L = 5.0\text{ mH}$		10	mJ
Repetitive avalanche current	I_{AR}	Current decaying linearly to zero in 1 μs Frequency limited by T_J maximum $V_A = 1.5 \times V_R$ typical		2.0	A

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum forward voltage drop See fig. 1	$V_{FM}^{(1)}$	1 A	$T_J = 25\text{ }^{\circ}\text{C}$	0.41	0.45	V
		2 A		0.46	0.50	
		1 A	$T_J = 125\text{ }^{\circ}\text{C}$	0.29	0.33	
		2 A		0.37	0.40	
Maximum reverse leakage current See fig. 2	$I_{RM}^{(1)}$	$V_R = \text{Rated } V_R$	$T_J = 25\text{ }^{\circ}\text{C}$	30	100	μA
			$T_J = 125\text{ }^{\circ}\text{C}$	10	30	mA
Maximum junction capacitance	C_T	$V_R = 5\text{ }V_{DC}$ (test signal range 100 kHz to 1 MHz) 25 °C		-	210	pF
Maximum voltage rate of charge	dV/dt	Rated V_R		-	10	V/ μs

Note

(1) Pulse width < 300 μs , duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction and storage temperature range	$T_J^{(1)}$, T_{Stg}			- 55 to 150	$^{\circ}\text{C}$
Typical thermal resistance, junction to PCB	$R_{thJL}^{(2)}$	DC operation		40	$^{\circ}\text{C/W}$
Maximum thermal resistance, junction to ambient	R_{thJA}			62	

Notes

(1) $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}}$ thermal runaway condition for a diode on its own heatsink

(2) Mounted 1" square PCB

FlipKY[®], 1 A
Chip Scale Package Schottky
Barrier Rectifier

Vishay High Power Products

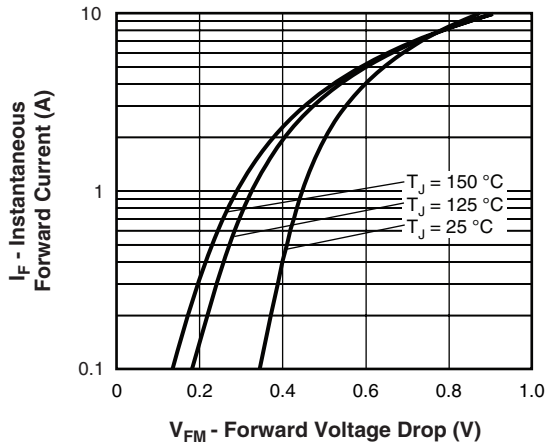


Fig. 1 - Maximum Forward Voltage Drop Characteristics (Per Leg)

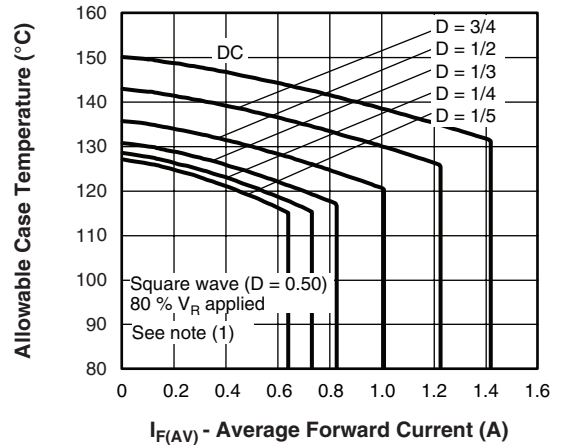


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

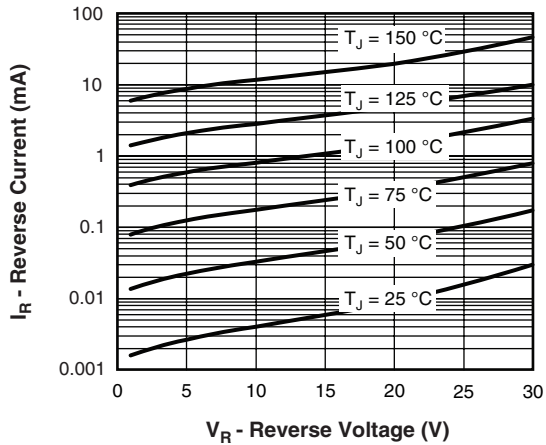


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage (Per Leg)

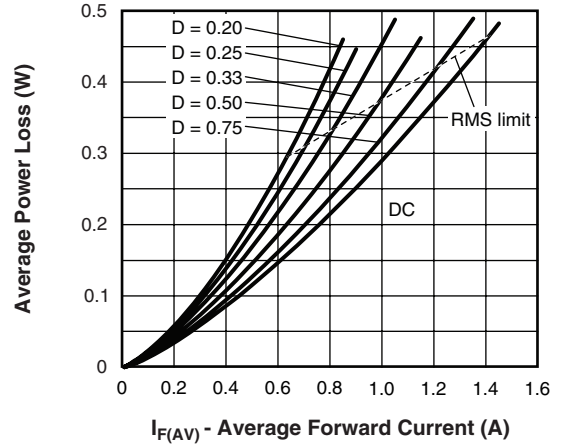


Fig. 5 - Forward Power Loss Characteristics (Per Leg)

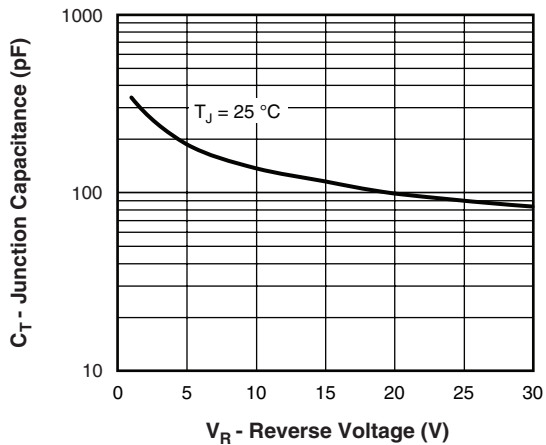


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

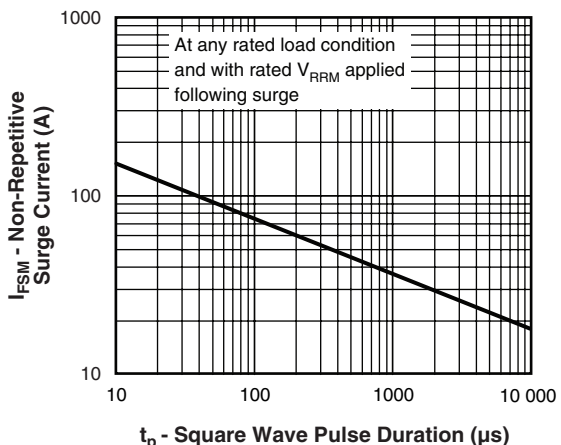


Fig. 6 - Maximum Non-Repetitive Surge Current (Per Leg)

Note

(1) Formula used: $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$;
 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); P_{dREV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at 80 % V_R applied

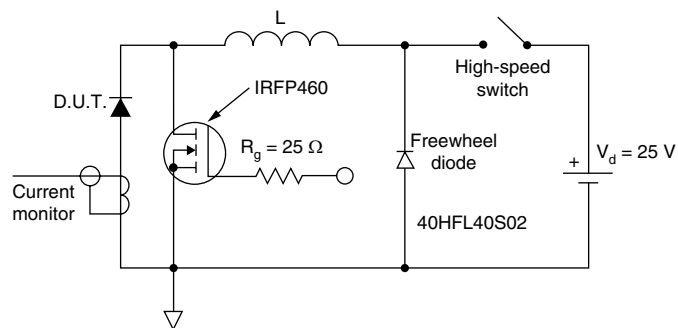


Fig. 7 - Unclamped Inductive Test Circuit

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95282
Part marking information	http://www.vishay.com/doc?95281
Packaging information	http://www.vishay.com/doc?95062



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